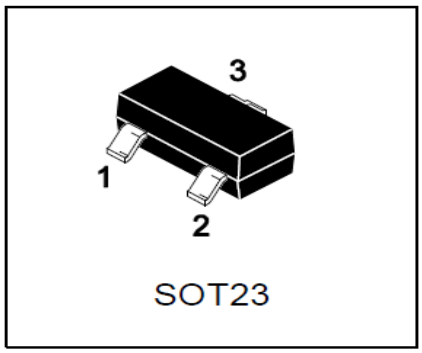
●硅 PNP 外延平面三极管



MARKING: Y2

PIN: 1、B, 2、E, 3、C

● 用途：

通用放大、开关

● 特点：

输出功率大

集电极电流大

与 SS8050 构成互补对管

●极限参数(Ta=25℃)

参数	符号	单位	规范值
耗散功率	Ptot	mW	300
集电极电流	Ic	mA	-1500
结　　温	T(j)	℃	150
存贮温度	Tstg	℃	-55~+150
集电极-基极电压	V_{CBO}	V	-40
集电极－发射极电压	V_{CEO}	V	-25
发射极－基极电压	V_{EBO}	V	-6

● 电参数(Ta=25℃)

参数符号	测试条件	最小值	最大值	单位
V_{CBO}	I_C = -100μA　I_E＝0	-40		V
V_{CEO}	I_C = -2mA　I_B＝0	-25		V
V_{EBO}	I_E = -100μA　I_C＝0	-6		V
I_{CBO}	V_{CB}＝-35V　I_E＝0		-0.1	μA
I_{CEO}	V_{CE}＝-20V　I_B＝0		-0.1	μA
I_{EBO}	V_{EB}＝-6V　I_C＝0		-0.1	μA
H_{FE}	V_{CE}＝-1V　I_C＝-100 mA	100	400	
V_{CE}(sat)	Ic= -800mA　I_B= -80mA		-0.5	V
V_{BE}(sat)	Ic= -800mA　I_B= -80mA		-1.2	V
f_T	V_{CE}＝-10V　I_C＝-50mA　F=30MHz	100		MH_Z

● H_{FE} 分档

Rank	P	Q	R
H_{FE}	100-200	150-300	200-400

●典型曲线图

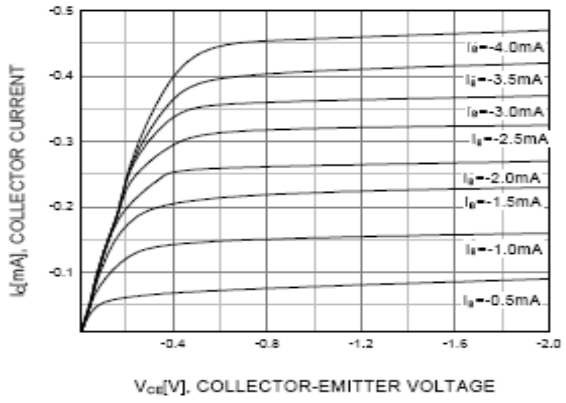


Figure 1. Static Characteristic

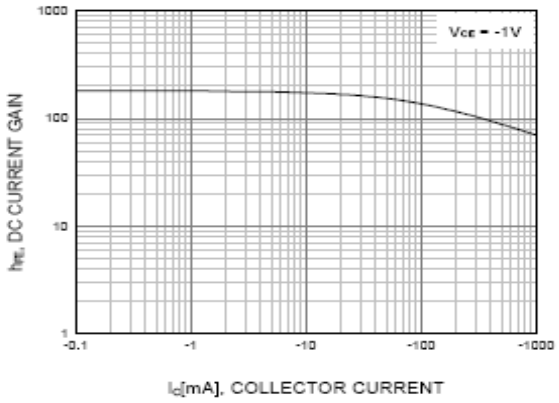


Figure 2. DC current Gain

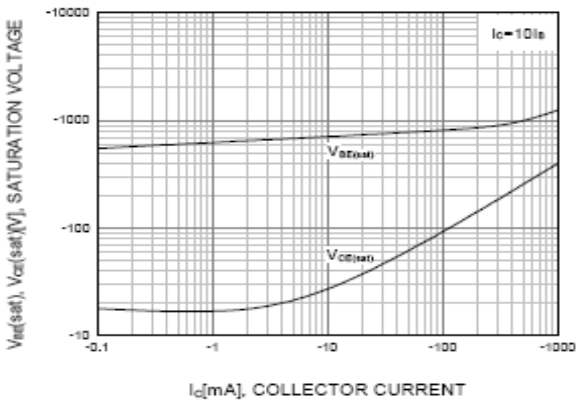


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

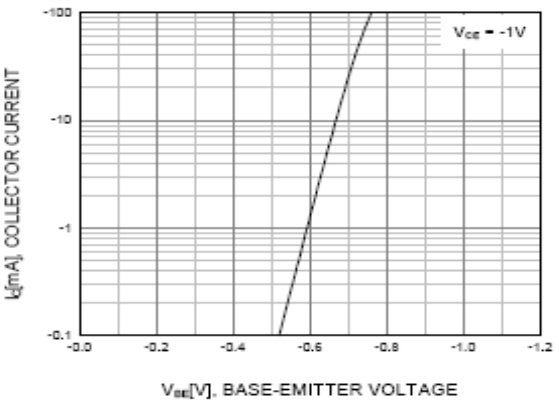


Figure 4. Base-Emitter On Voltage

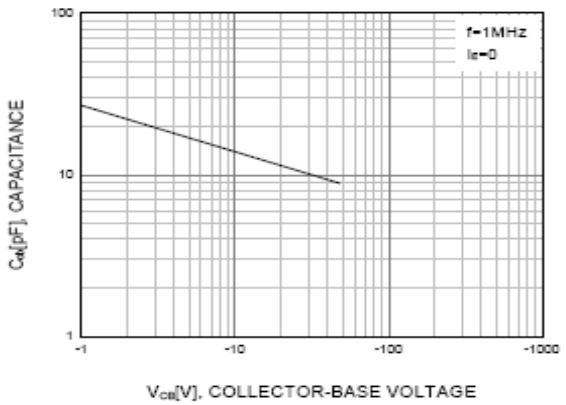


Figure 5. Collector Output Capacitance

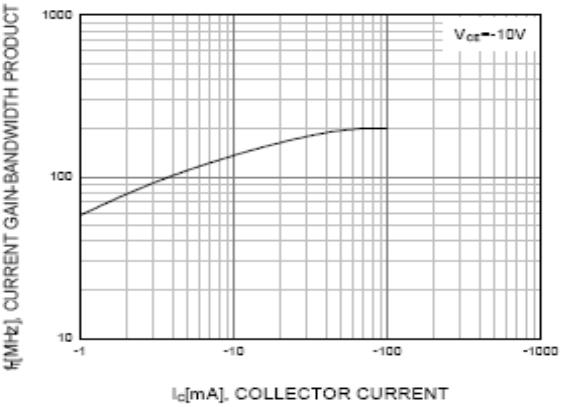
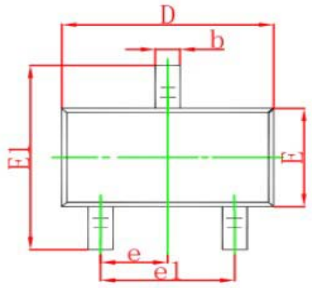
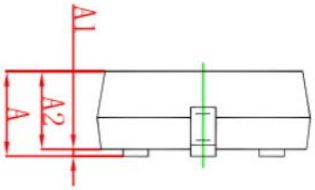


Figure 6. Current Gain Bandwidth Product

- **SOT-23 外形封装尺寸**





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079